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TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

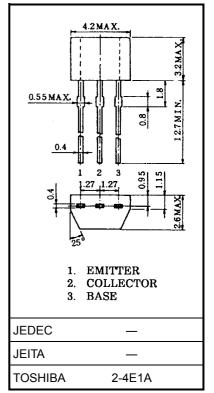
2SC3267

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: V_{CE} (sat) = 0.5 V (max) @I_C = 2 A
- Complementary to 2SA1297

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	20	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	Ι _C	2	А
Base current	Ι _Β	0.5	А
Collector power dissipation	P _C	400	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C



Weight: 0.13 g (typ.)

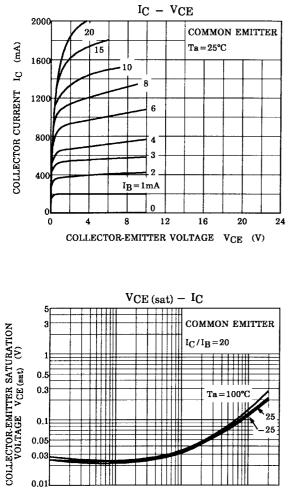
Electrical Characteristics (Ta = 25°C)

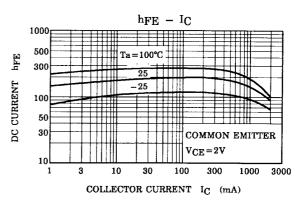
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 20 V, I_E = 0$			0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 6 V, I_{C} = 0$	_	_	0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	20		_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_E = 0.1 \text{ mA}, I_C = 0$	6		_	V
DC current gain	h _{FE (1)} (Note)	$V_{CE} = 2 \text{ V}, \text{ I}_{C} = 100 \text{ mA}$	120	_	700	
	h _{FE (2)}	$V_{CE} = 2 V, I_C = 2 A$	75		_	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = 2 \text{ A}, I_{B} = 0.1 \text{ A}$	_		0.5	V
Base-emitter voltage	V _{BE}	$V_{CE} = 2 V, I_C = 0.1 A$	_		0.85	V
Transition frequency	f _T	$V_{CE} = 2 \text{ V}, \text{ I}_{C} = 0.5 \text{ A}$	_	120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	30		pF

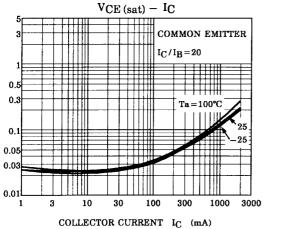
Note: hFE (1) classification Y: 120~240, GR: 200~400, BL: 350~700

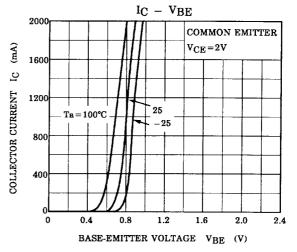
Unit: mm

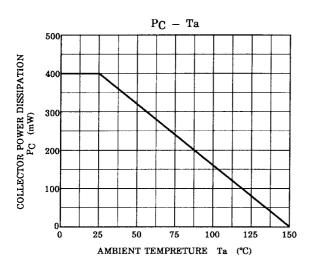
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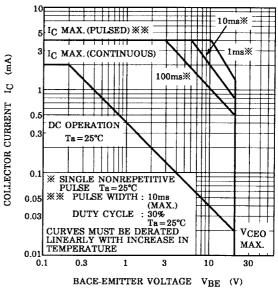












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